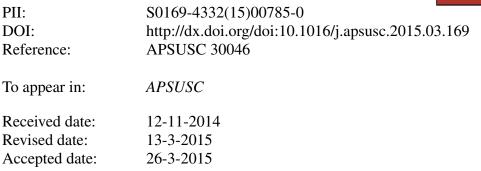
## Accepted Manuscript

Title: Photo-detection Characteristics of  $In-Zn-O/SiO_x/n-Si$ Hetero-junctions

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## ACCEPTED MANUSCRIPT

• Semiconductor-insulator-semiconductor (SIS) hetero-junction photodetection devices

contained indium-zinc-oxide (IZO) layer was fabricated.

• IZO film grown at 250°C possessed a low resistivity and a high optical transmittance in

wavelength range from UV to NIR.

• The IZO/SiO<sub>x</sub>/*n*-Si SIS photodetectors with photoresponse of 35 AW<sup>-1</sup> and 6.15 AW<sup>-1</sup>

were separately achieved at visible light and UV light.

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